

ST13005

High voltage fast-switching NPN power transistor

Features

- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Electronic ballast for fluorescent lighting
- Switch mode power supplies

Description

The device is manufactured using high voltage multi-epitaxial planar technology for high switching speeds and medium voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

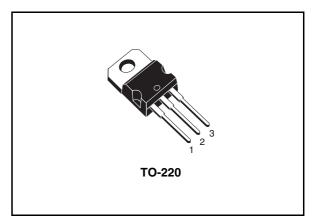


Figure 1. Internal schematic diagram

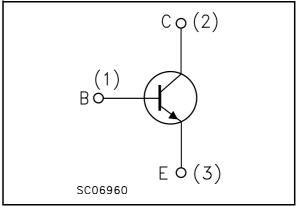


Table	1.	Device	summary
Table		DCVICC	Summary

Order code	Marking ⁽¹⁾	Package	Packaging
ST13005	ST13005A	TO-220	Bulk
ST13005	ST13005B	TO-220	Bulk

1. Product is pre-selected in DC current gain (group A and group B). STMicroelectronics reserves the right to ship either groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery details.

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1 Electrical ratings

Table 2.	Absolute maximum rating

Symbol	Parameter	Value	Unit
V _{CES}	Collector-emitter voltage (V _{BE} = 0)	700	V
V _{CEO}	Collector-emitter voltage ($I_B = 0$)	400	V
V _{EBO}	Emitter-base voltage (I _C = 0)	9	V
Ι _C	Collector current	4	А
I _{CM}	Collector peak current (t _P < 5ms)	8	А
۱ _B	Base current	2	А
I _{BM}	Base peak current (t _P < 5ms)	4	А
P _{tot}	Total dissipation at $T_c = 25^{\circ}C$	75	W
T _{stg}	Storage temperature	-65 to 150	°C
Τ _J	Max. operating junction temperature	150	°C

2 Electrical characteristics

 $(T_{case} = 25^{\circ}C \text{ unless otherwise specified})$

Symbol Parameter Test Conditions Min. Typ. Max. Unit l_{CES} Collector cut-off current ($v_{BE} = 0$) $V_{CE} = 700 \lor$ $v_{CE} = 700 \lor$ $T_{C} = 125^{\circ}$ C I_{CS} I_{SS}	Table 5.	Electrical characteristics						
	Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit
$\frac{ V_{BE} ^{-1}}{ V_{CE}(sus) ^{(1)}} = \frac{ V_{BE} ^{-1}}{ V_{CE} ^{-1}} = \frac{ V_{CE} ^{-1}}{ V_{CE} ^{-1}} = \frac{ V_{CE} ^{-1}}{ V_{CE} ^{-1}} = \frac{ V_{CE} ^{-1}}{ V_{CE}(sus) ^{(1)}} = \frac{ V_{CE} ^{-1}}{ V_{CE} ^{-1}} = V_{CE$	loss	Collector cut-off current					1	mA
$\frac{1}{1} \frac{1}{1} = \frac{1}{1} \frac{1}{1} \frac{1}{1} \frac{1}{1} = \frac{1}{1} \frac{1}{1$	-0E3	(V _{BE} = 0)	V _{CE} =700 V	T _C = 125°C			5	mA
	I _{EBO}		V _{EB} = 9 V				1	mA
$\begin{split} & V_{CE(sat)}^{(1)} \begin{bmatrix} Collector-emitter \\ saturation voltage \end{bmatrix} \begin{bmatrix} I_C = 2 & A & I_B = 0.5 & A \\ I_C = 4 & A & I_B = 1 & A \end{bmatrix} \begin{bmatrix} 0.6 & V \\ 1 & V \end{bmatrix} \\ & V_{BE(sat)}^{(1)} \end{bmatrix} & Base-emitter saturation \\ voltage \end{bmatrix} \begin{bmatrix} I_C = 1 & A & I_B = 0.2 & A \\ I_C = 2 & A & I_B = 0.5 & A \end{bmatrix} \begin{bmatrix} 1.2 & V \\ 1.6 & V \end{bmatrix} \\ & I_C = 2 & A & I_B = 0.5 & A \end{bmatrix} \begin{bmatrix} 1.2 & V \\ 1.6 & V \end{bmatrix} \\ & I_C = 1 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 1 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 2 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 2 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 2 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 2 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 2 & A & V_{CE} = 5 & V \end{bmatrix} \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = 125 & V \\ & I_C = 1 & V_C = $	V _{CEO(sus)} ⁽¹⁾	sustaining voltage	I _C =10 mA		400			<
		Collector omitter	I _C = 1 A	I _B = 0.2 A			0.5	V
$I_{C} = 4 A \qquad I_{B} = 1 A \qquad 1 \qquad V$ $V_{BE(sat)}^{(1)} Base-emitter saturation voltage \qquad I_{C} = 1 A \qquad I_{B} = 0.2 A \\ I_{C} = 2 A \qquad I_{B} = 0.5 A \qquad 1.2 \qquad V$ $I_{C} = 2 A \qquad I_{B} = 0.5 A \qquad 1.6 \qquad V$ $I_{C} = 1 A \qquad V_{CE} = 5 V \qquad 1.6 \qquad V$ $I_{C} = 1 A \qquad V_{CE} = 5 V \qquad 1.6 \qquad V$ $Group A \qquad 15 \qquad 32 \\ Group B \qquad 27 \qquad 45 \\ I_{C} = 2 A \qquad V_{CE} = 5 V \qquad 8 \qquad 40 \qquad V$ $I_{C} = 2 A \qquad V_{CE} = 5 V \qquad 8 \qquad 40 \qquad V$	V _{CE(sat)} ⁽¹⁾		I _C = 2 A	I _B = 0.5 A			0.6	V
		outeration voltage	$I_C = 4 A$	I _B = 1 A			1	V
$h_{FE}^{(1)(2)} \begin{array}{c ccccccccccccccccccccccccccccccccccc$	V (1)	Base-emitter saturation	I _C = 1 A	I _B = 0.2 A			1.2	V
$ \begin{array}{ccccccccccc} h_{FE}{}^{(1)(2)} & DC \mbox{ current gain} & & & & & & & & & & & & & & & & & & &$	VBE(sat)	voltage	$I_C = 2 A$	I _B = 0.5 A			1.6	V
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			I _C = 1 A	V _{CE} = 5 V				
$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	ь (1)(2)	DC current gain	Group A		15		32	
tsResistive loadIC = 2 AV_{CC} = 125 VtsStorage timeIB1 = - IB2 = 0.4 A1.53	"FE YYY				27		45	
t_s Storage time $I_{B1} = -I_{B2} = 0.4 \text{ A}$ 1.5 3 µs			I _C = 2 A	V _{CE} = 5 V	8		40	
		Resistive load	I _C = 2 A	V _{CC} = 125 V				
t_f Fall time $t_p = 30 \ \mu s$ 0.2 μs	t _s	Storage time	$I_{B1} = -I_{B2} = 0$	0.4 A	1.5		3	μs
	t _f	Fall time	t _p = 30 μs			0.2		μs

Table 3. Electrical characteristics

1. Pulsed duration = 300 ms, duty cycle £1.5%

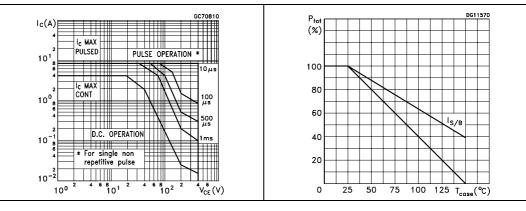
 Product is pre-selected in DC current gain (group A and group B). STMicroelectronics reserves the right to ship either groups according to production availability. Please contact your nearest STMicroelectronics sales office for delivery details.



2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Derating curve





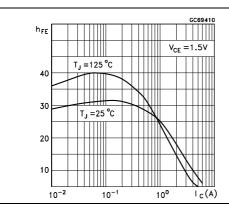


Figure 5. DC current gain

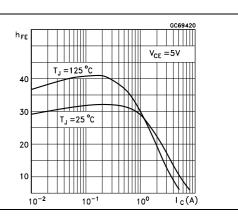
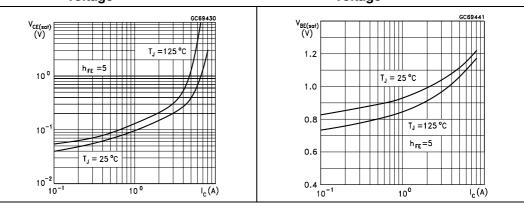


Figure 6. Collector-emitter saturation Figure 7. voltage

Base-emitter saturation voltage



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GC70840

 $V_{Clamp} = 200 V$

 $V_{BE(off)} = -5V$

 $h_{FE} = 5$ $R_{BB} = 0 \Omega$

Figure 8. Inductive load fall time Figure 9.

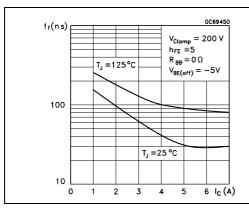
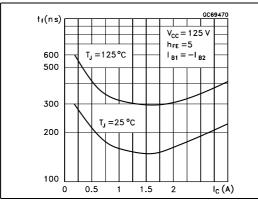
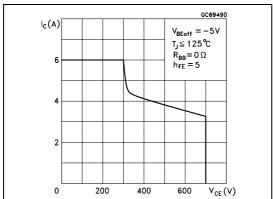


Figure 10. Resistive load fall time

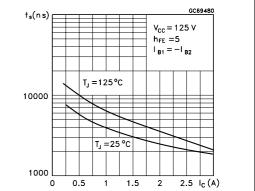


1000 0 0.5 1

Figure 12. **Reverse biased operating** area



2 5 6 I_C(A) 1 3 4 Figure 11. Resistive load storage time



Inductive load storage time

T_J = 125 °C

T_J = 25 °C

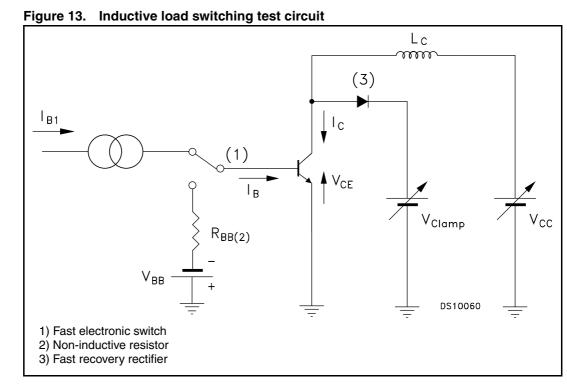
 $t_s(\mu s)$

1

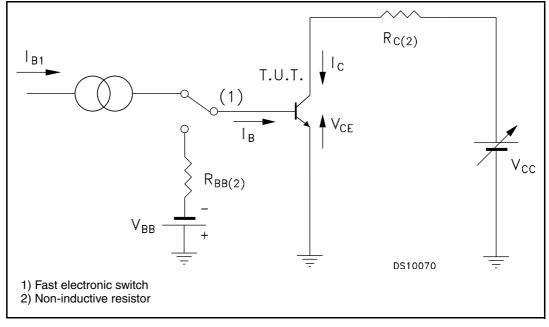
0.1

0

3 Test circuit









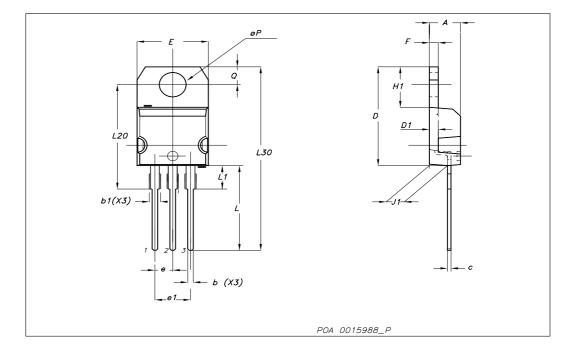
4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com



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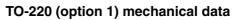
Dim		mm			inch		
	Min	Тур	Max	Min	Тур	Max	
Α	4.40		4.60	0.173		0.181	
b	0.61		0.88	0.024		0.034	
b1	1.14		1.70	0.044		0.066	
С	0.49		0.70	0.019		0.027	
D	15.25		15.75	0.6		0.62	
D1		1.27			0.050		
E	10		10.40	0.393		0.409	
е	2.40		2.70	0.094		0.106	
e1	4.95		5.15	0.194		0.202	
F	1.23		1.32	0.048		0.051	
H1	6.20		6.60	0.244		0.256	
J1	2.40		2.72	0.094		0.107	
L	13		14	0.511		0.551	
L1	3.50		3.93	0.137		0.154	
L20		16.40			0.645		
L30		28.90			1.137		
ØP	3.75		3.85	0.147		0.151	
Q	2.65		2.95	0.104		0.116	

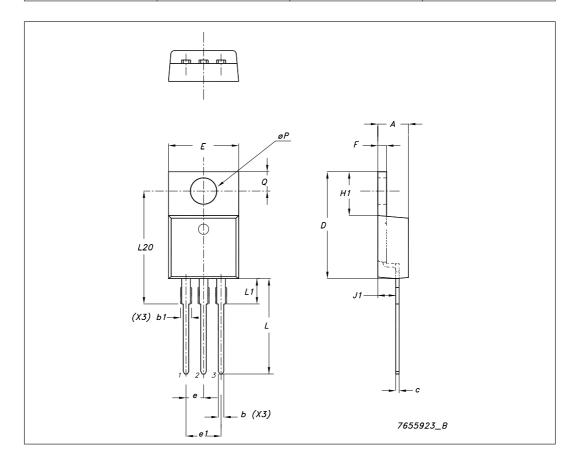


TO-220 mechanical data



Dim		mm	
Dilli	Min	Тур	Мах
А	4.47		4.67
b	0.70		0.91
b1	1.17		1.37
С	0.31		0.53
D	14.60		15.70
E	9.96		10.36
е		2.54	
e1	4.98	5.08	5.18
F	1.17		1.37
H1	6.10		6.80
J1	2.52		2.82
L	12.70		13.80
L1	3.20		3.96
L20	15.21		16.77
øP	3.73		3.94
Q	2.59		2.89







5 Revision history

Table 4. Document revision history

Date	Revision	Changes
21-Jun-2004	6	
22-Aug-2007	7	Updated mechanical data on page 10 according to PCN APM-PWR/07/2804



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